



ALPHA & OMEGA
SEMICONDUCTOR



AO9926E

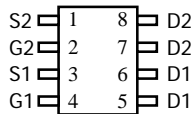
Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

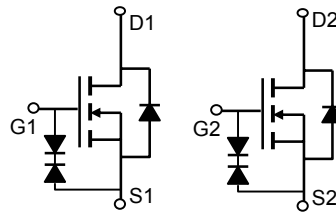
The AO9926E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AO9926E is Pb-free (meets ROHS & Sony 259 specifications). AO9926EL is a Green Product ordering option. AO9926E and AO9926EL are*

Features

- V_{DS} (V) = 20V
- I_D = 8A (V_{GS} = 4.5V)
- $R_{DS(ON)} < 21m\Omega$ (V_{GS} = 4.5V)
- $R_{DS(ON)} < 25m\Omega$ (V_{GS} = 2.5V)
- $R_{DS(ON)} < 33m\Omega$ (V_{GS} = 1.8V)
- ESD Rating: 2000V HBM



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current ^B	I_{DM}	30	
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	74	
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	40	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$T_J=55^\circ\text{C}$			5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 4.5\text{V}$			± 1	μA
		$V_{DS}=0\text{V}$, $V_{GS}=\pm 8\text{V}$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.4	0.6	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}$, $I_D=8\text{A}$		18	21	$\text{m}\Omega$
		$T_J=125^\circ\text{C}$		25	30	
		$V_{GS}=2.5\text{V}$, $I_D=7\text{A}$		21	25	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}$, $I_D=6\text{A}$		25	33	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=8\text{A}$		29		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.76	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance			1160		pF
C_{oss}	Output Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=10\text{V}$, $f=1\text{MHz}$		187		pF
C_{rss}	Reverse Transfer Capacitance			146		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.5		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge			16		nC
Q_{gs}	Gate Source Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=10\text{V}$, $I_D=8\text{A}$		0.8		nC
Q_{gd}	Gate Drain Charge			3.8		nC
$t_{D(on)}$	Turn-On DelayTime			6.2		ns
t_r	Turn-On Rise Time	$V_{GS}=5\text{V}$, $V_{DS}=10\text{V}$, $R_L=1.25\Omega$,		12.7		ns
$t_{D(off)}$	Turn-Off DelayTime	$R_{GEN}=3\Omega$		51.7		ns
t_f	Turn-Off Fall Time			16		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=8\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		17.8		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=8\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		6.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

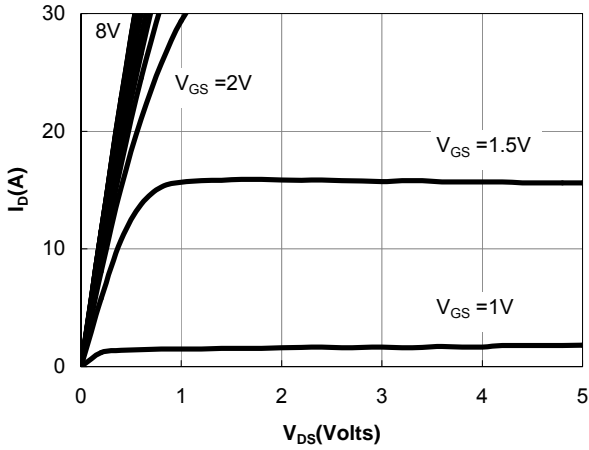


Figure 1: On-Regions Characteristics

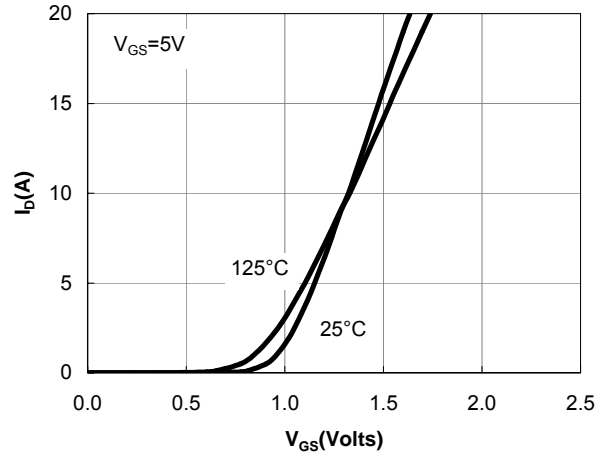


Figure 2: Transfer Characteristics

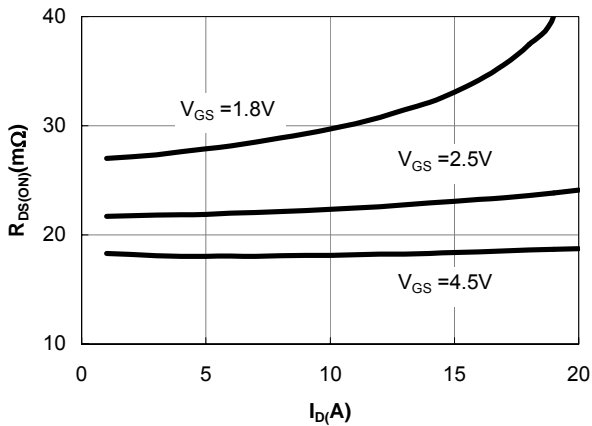


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

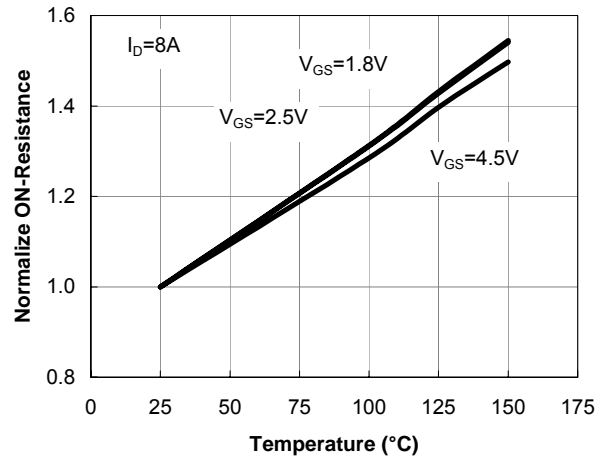


Figure 4: On-Resistance vs. Junction Temperature

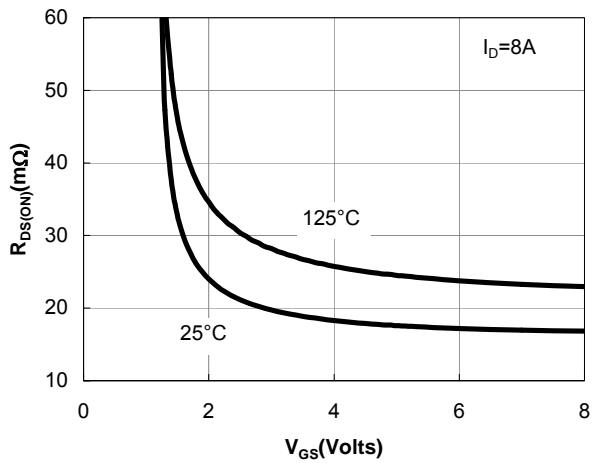


Figure 5: On-Resistance vs. Gate-Source Voltage

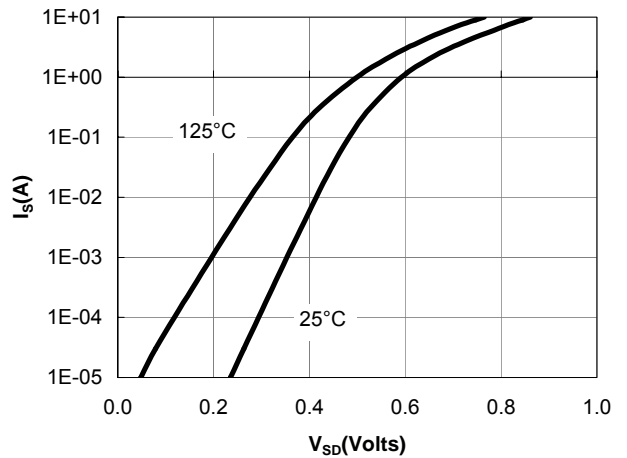


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

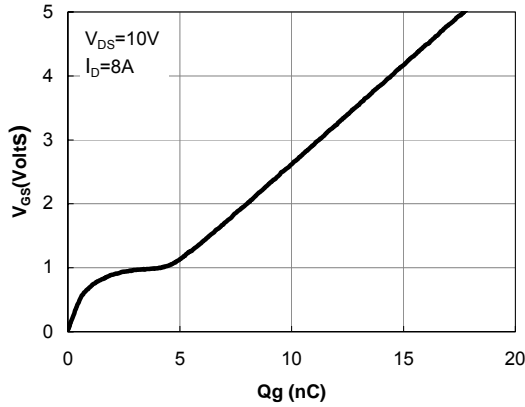


Figure 7: Gate-Charge Characteristics

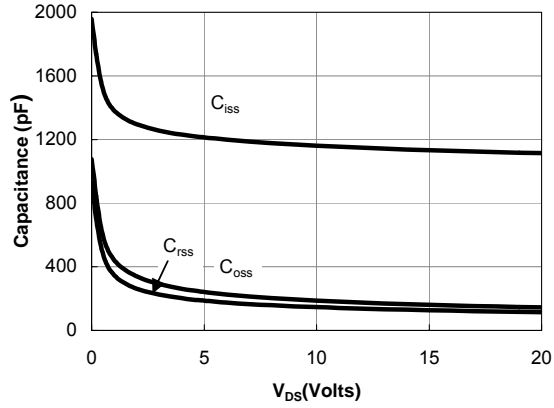


Figure 8: Capacitance Characteristics

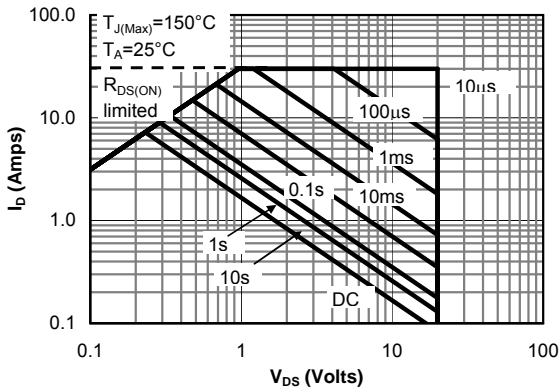


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

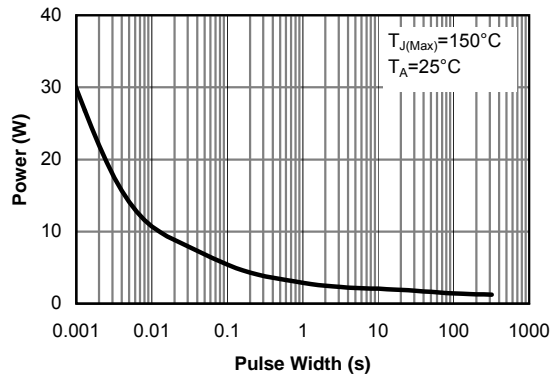


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

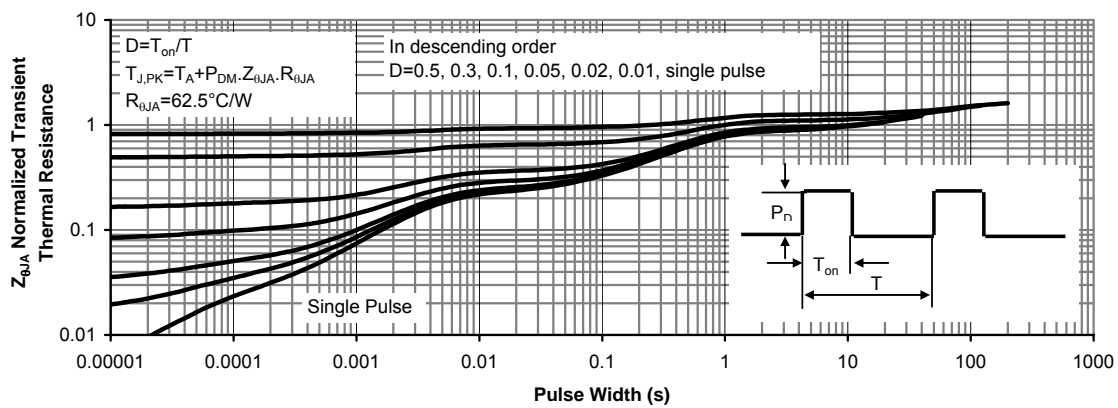


Figure 11: Normalized Maximum Transient Thermal Impedance